

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

OptiMOS™

OptiMOS™ 3 Power-Transistor, 150 V
IPT059N15N3

Data Sheet

Rev. 2.1
Final

1 Description

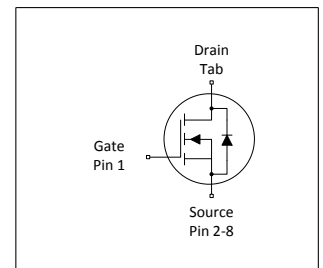
Features

- N-channel, normal level
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC ¹⁾ for target application
- Ideal for high-frequency switching and synchronous rectification
- Halogen-free according to IEC61249-2-21



Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	150	V
$R_{DS(on),max}$	5.9	mΩ
I_D	155	A



Type / Ordering Code	Package	Marking	Related Links
IPT059N15N3	PG-HSOF-8-1	059N15N3	-

¹⁾ J-STD20 and JESD22

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2 Maximum ratings

at $T_j = 25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings
at 25 °C

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	155 110	A	$T_C=25\text{ °C}$ $T_C=100\text{ °C}$
Pulsed drain current ¹⁾	$I_{D,pulse}$	-	-	620	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	E_{AS}	-	-	520	mJ	$I_D=150\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	375	W	$T_C=25\text{ °C}$
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

3 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	0.2	0.4	K/W	-
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}	-	-	62	K/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ²⁾	R_{thJA}	-	-	40	K/W	-

¹⁾ See figure 3

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

4 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	150	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2	3	4	V	$V_{DS}=V_{GS}$, $I_D=270\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=25\text{ }^\circ\text{C}$ $V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=125\text{ }^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	1	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	5 5.2	5.9 6.2	m Ω	$V_{GS}=10\text{ V}$, $I_D=150\text{ A}$ $V_{GS}=8\text{ V}$, $I_D=75\text{ A}$
Gate resistance	R_G	-	2.1	3.2	Ω	-
Transconductance	g_{fs}	86	172	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=150\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	5400	7182	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	630	838	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	10	19	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	25	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=100\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	35	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=100\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	46	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=100\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	14	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=100\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

Table 6 Gate charge characteristics ¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	29	-	nC	$V_{DD}=75\text{ V}$, $I_D=100\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	Q_{gd}	-	11	-	nC	$V_{DD}=75\text{ V}$, $I_D=100\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	24	-	nC	$V_{DD}=75\text{ V}$, $I_D=100\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	Q_g	-	69	92	nC	$V_{DD}=75\text{ V}$, $I_D=100\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	$V_{DD}=75\text{ V}$, $I_D=100\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge	Q_{oss}	-	178	-	nC	$V_{DD}=75\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	155	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	620	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.94	1.2	V	$V_{GS}=0\text{ V}$, $I_F=150\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery time	t_{rr}	-	146	292	ns	$V_R=75\text{ V}$, $I_F=I_S$, $di_F/dt=100\text{ A/}\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	478	-	nC	$V_R=75\text{ V}$, $I_F=I_S$, $di_F/dt=100\text{ A/}\mu\text{s}$

5 Electrical characteristics diagrams

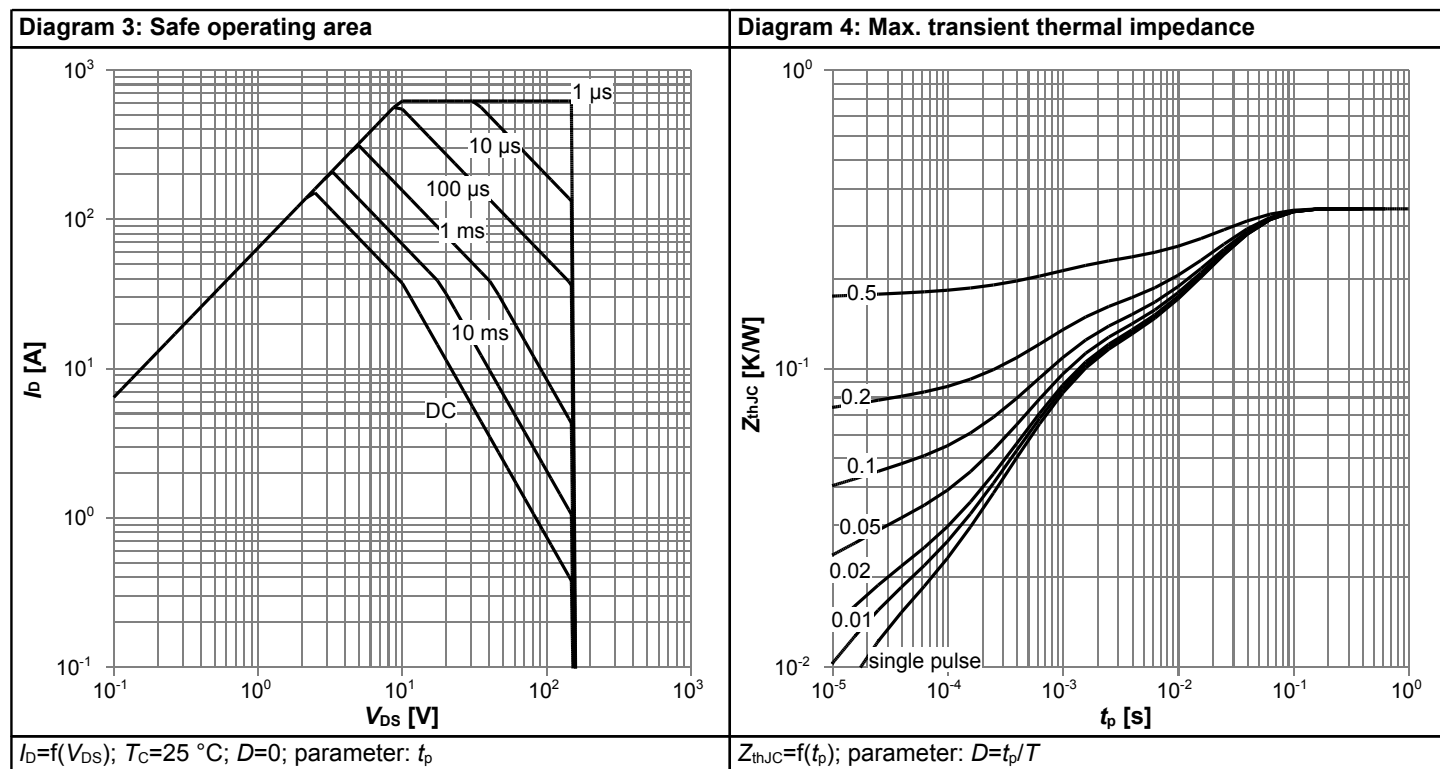
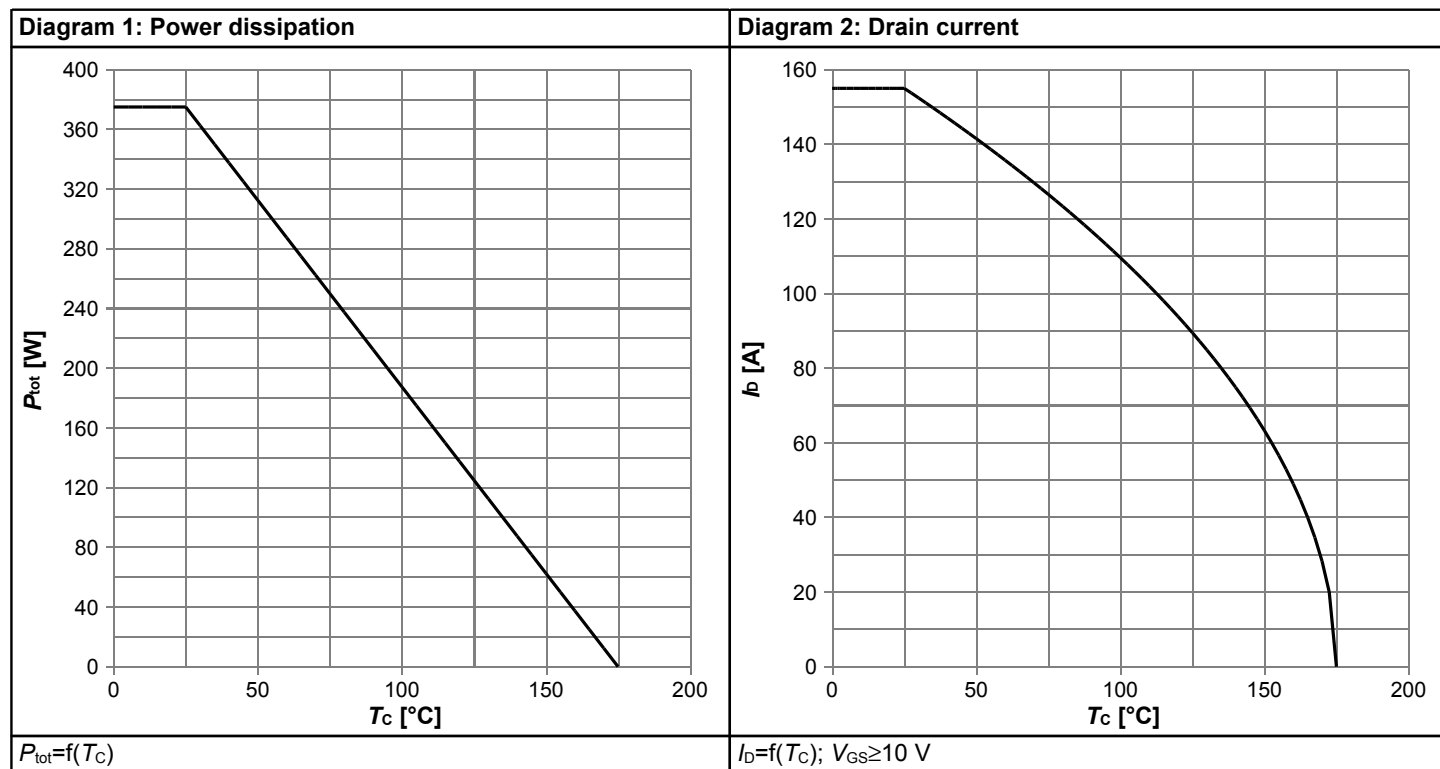


Diagram 5: Typ. output characteristics

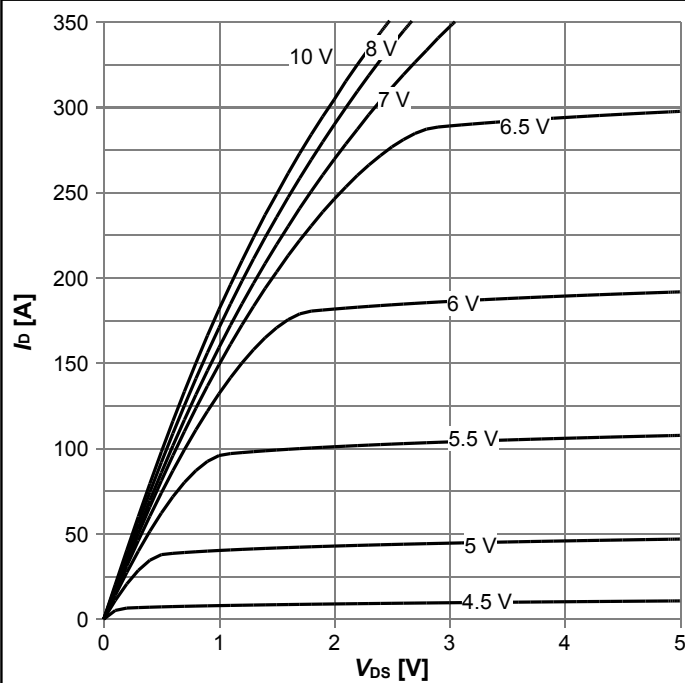

 $I_D = f(V_{DS}); T_j = 25\text{ °C}; \text{parameter: } V_{GS}$

Diagram 6: Typ. drain-source on resistance

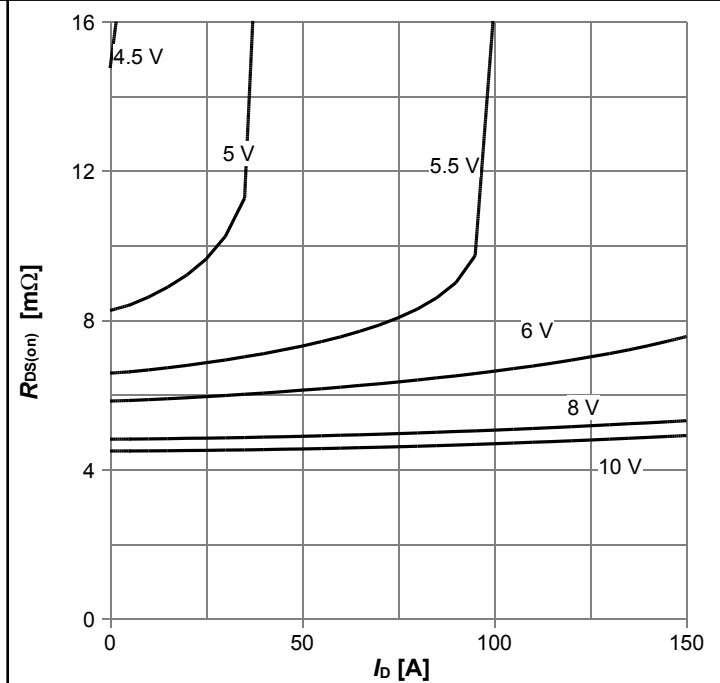

 $R_{DS(on)} = f(I_D); T_j = 25\text{ °C}; \text{parameter: } V_{GS}$

Diagram 7: Typ. transfer characteristics

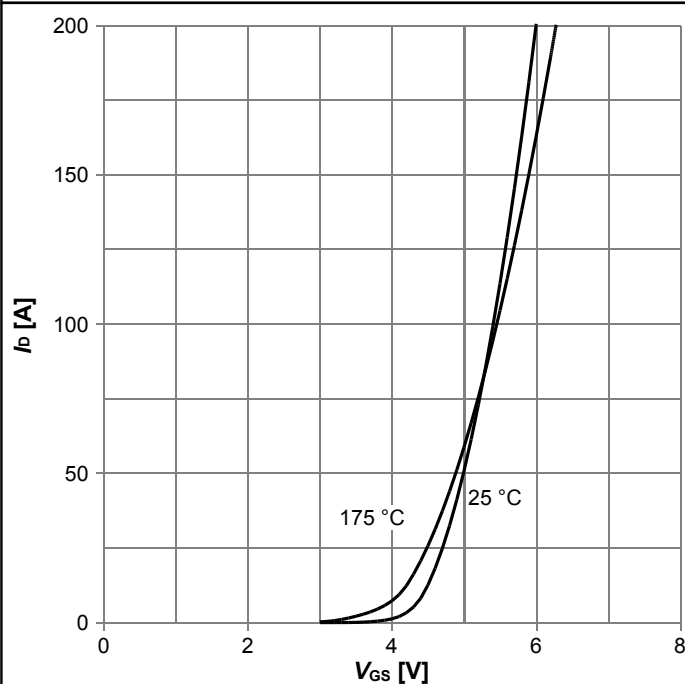

 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}; \text{parameter: } T_j$

Diagram 8: Typ. forward transconductance

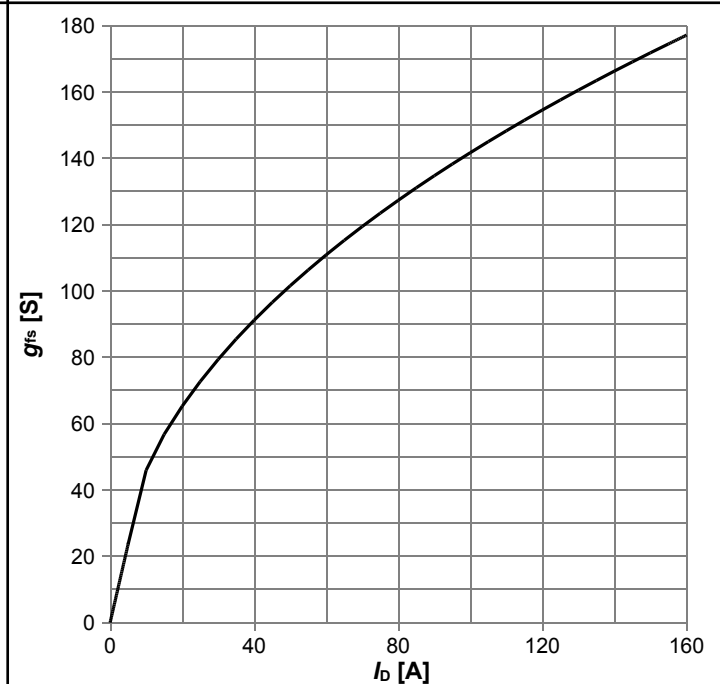
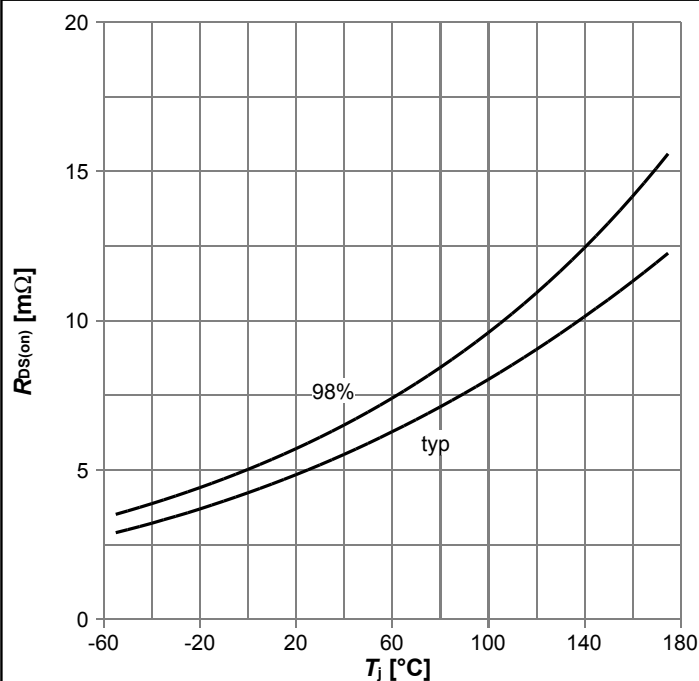
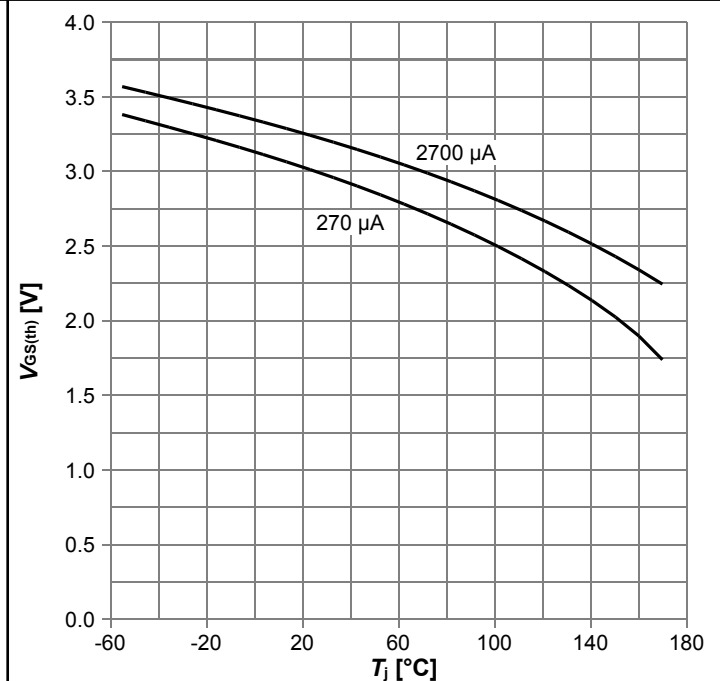

 $g_{fs} = f(I_D); T_j = 25\text{ °C}$

Diagram 9: Drain-source on-state resistance



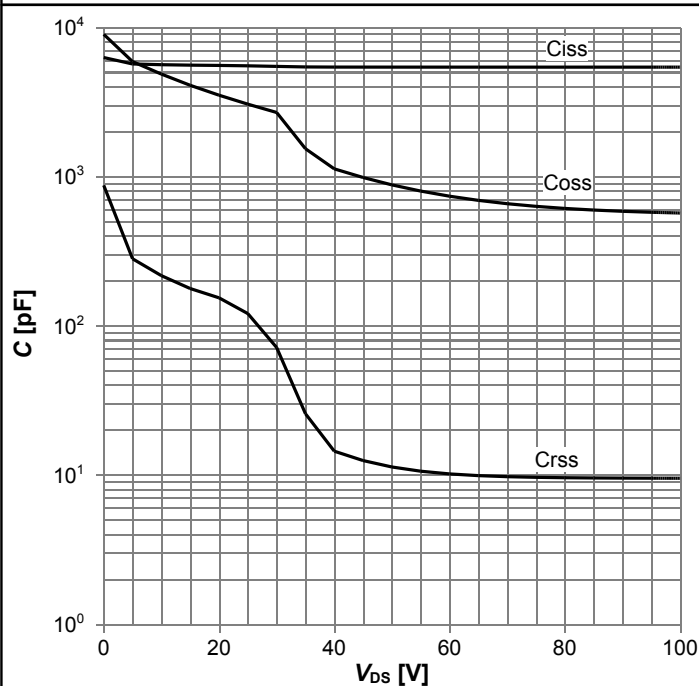
$$R_{DS(on)} = f(T_j); I_D = 150 \text{ A}; V_{GS} = 10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage



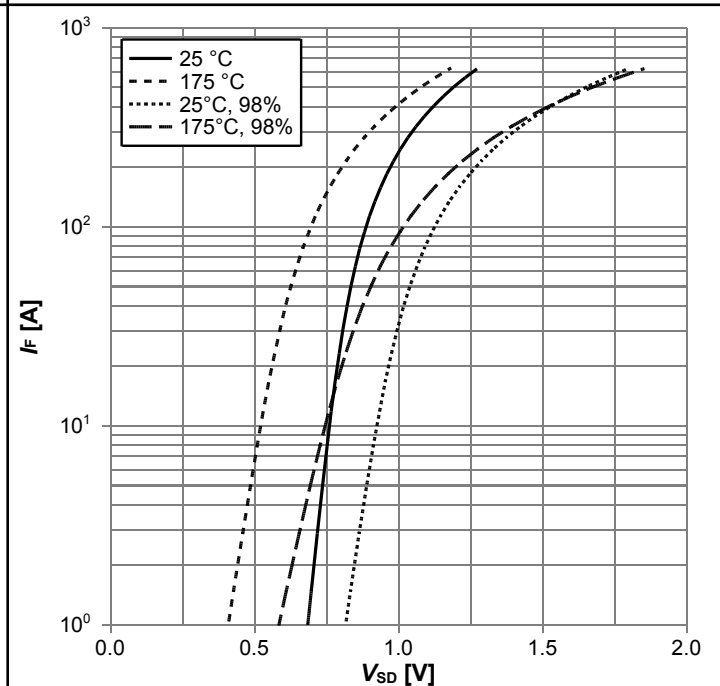
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; \text{parameter: } I_D$$

Diagram 11: Typ. capacitances



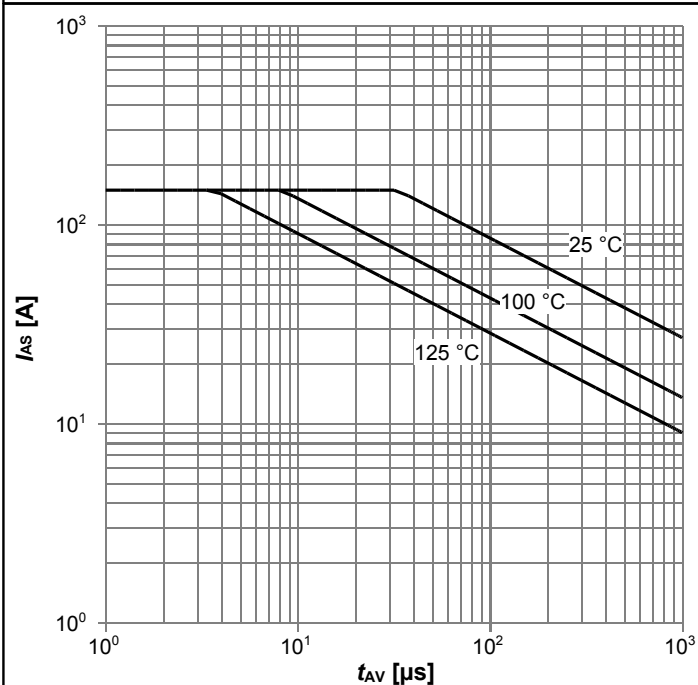
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 12: Forward characteristics of reverse diode



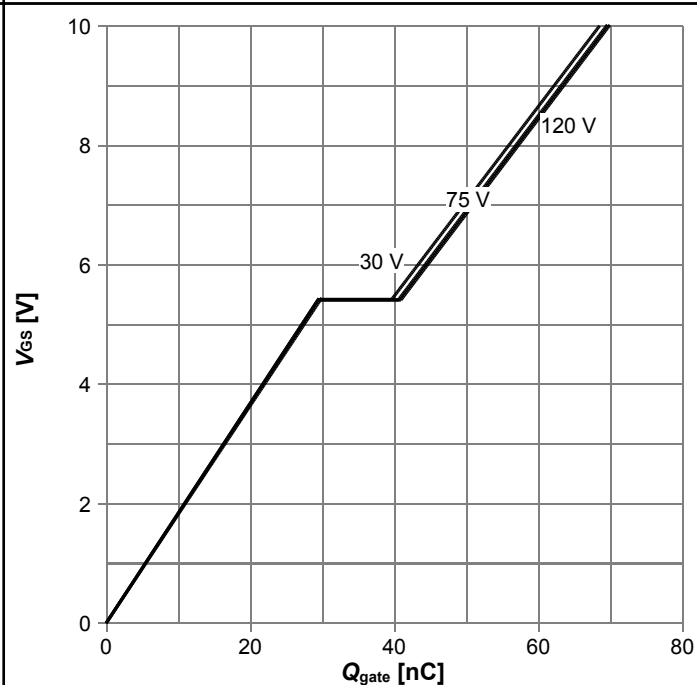
$$I_F = f(V_{SD}); \text{parameter: } T_j$$

Diagram 13: Avalanche characteristics



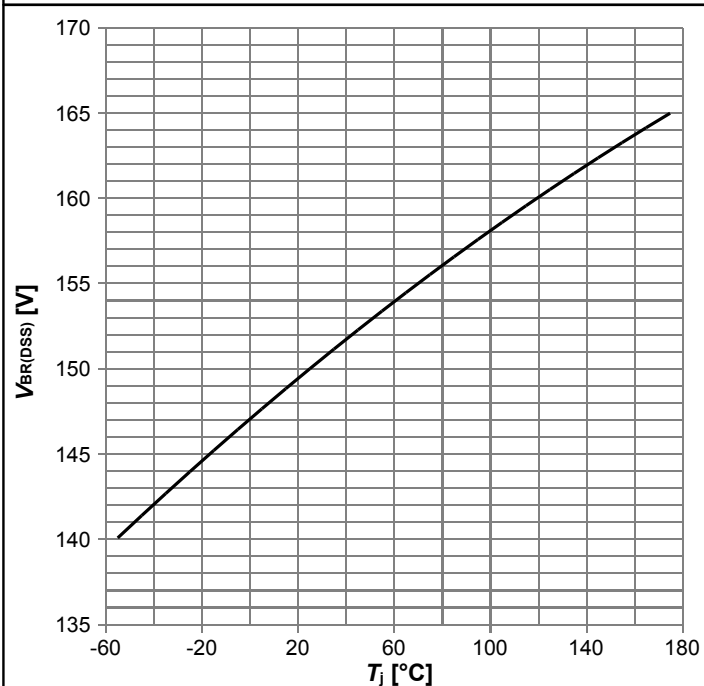
$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega; \text{parameter: } T_{j(\text{start})}$$

Diagram 14: Typ. gate charge



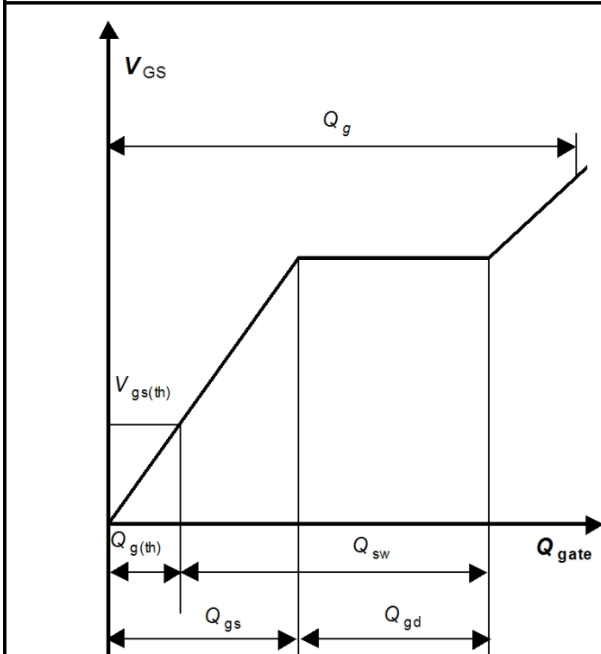
$$V_{GS}=f(Q_{\text{gate}}); I_D=100\ \text{A pulsed}; \text{parameter: } V_{DD}$$

Diagram 15: Drain-source breakdown voltage

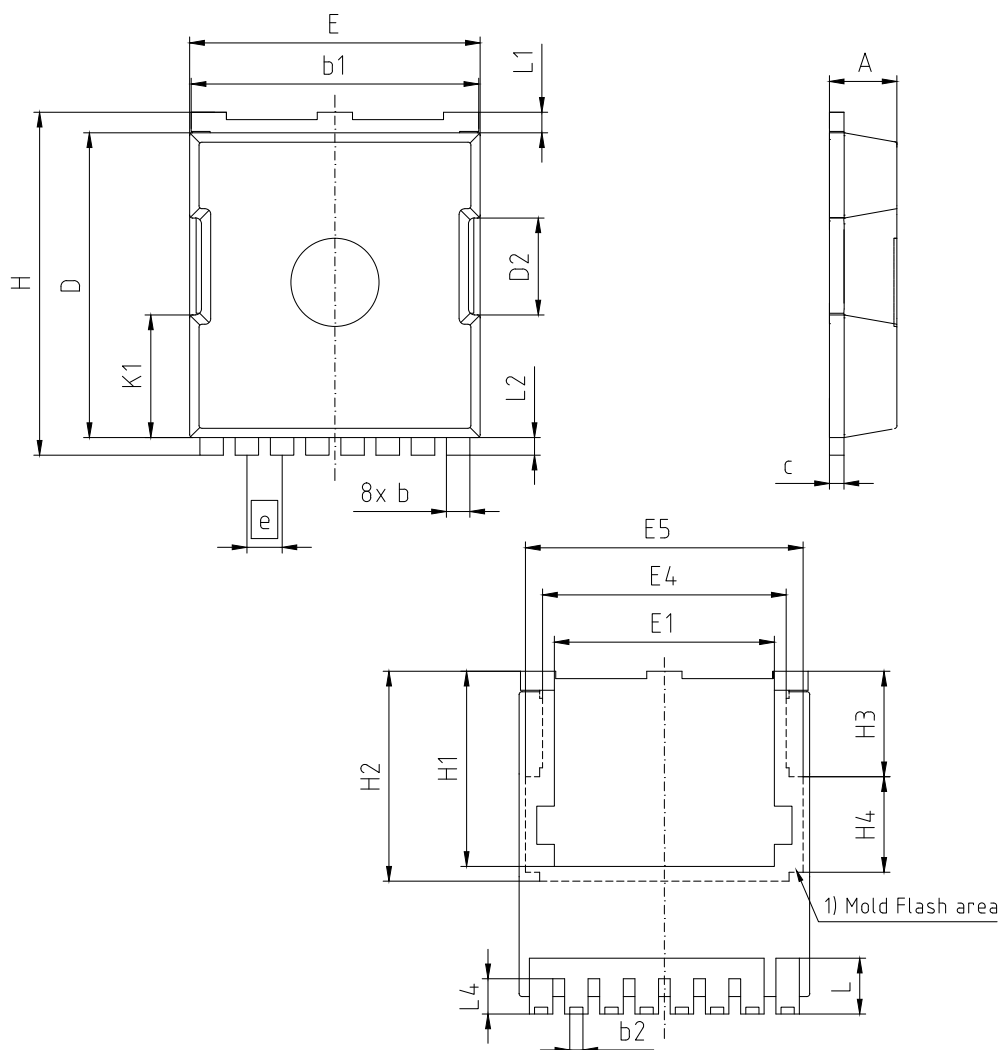


$$V_{BR(DSS)}=f(T_J); I_D=1\ \text{mA}$$

Gate charge waveforms



6 Package Outlines



1) partially covered with Mold Flash

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.40	0.087	0.094
b	0.70	0.90	0.028	0.035
b1	9.70	9.90	0.382	0.390
b2	0.42	0.50	0.017	0.020
c	0.40	0.60	0.016	0.024
D	10.28	10.58	0.405	0.416
D2	3.30		0.130	
E	9.70	10.10	0.382	0.398
E1	7.50		0.295	
E4	8.50		0.335	
E5	9.46		0.372	
e	1.20 (BSC)		0.047 (BSC)	
H	11.48	11.88	0.452	0.468
H1	6.55	6.75	0.258	0.266
H2	7.15		0.281	
H3	3.59		0.141	
H4	3.26		0.128	
N	8		8	
K1	4.18		0.165	
L	1.60	2.10	0.063	0.083
L1	0.50	0.90	0.020	0.035
L2	0.50	0.70	0.020	0.028
L4	1.00	1.30	0.039	0.051

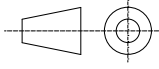
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SCALE 0 2 4mm	
EUROPEAN PROJECTION 	
ISSUE DATE 14-06-2013	
REVISION 01	

Figure 1 Outline PG-HSOF-8-1, dimensions in mm/inches

Revision History

IPT059N15N3

Revision: 2014-02-07, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2014-01-27	Release of final version
2.1	2014-02-07	Insert additional typ value (Rthjc) and max values (Crss,trr, Rg,Qg, Coss, Ciss)

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Published by

Infineon Technologies AG

81726 München, Germany

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